

A

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A

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D

TMR电容：设置过流保护延迟
TMR电阻100K：禁止过流保护
TMR悬空：最快过流保护延迟

$CTMR = 82u * 48u / 1.2 = 3.3nF$

$R_{imon} = V(imon) * R_{set} / ((V_{sns} + V_{os_set}) * 0.9)$
 $R_{imon} = 3 * 100 / ((50 * 0.0005 + 0.2mV) * 0.9) = 13.3K$
 $V_{sns} = I_{oc} * R_{sns}$
 $V_{os_set} = 200uV$

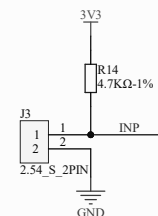
$R_{ISCP} = I_{sc} * R_{sns} / 15.6u - 600$
 $R_{ISCP} = 104 * 0.5mR / 15.6u - 600 = 2733$

短路保护104A

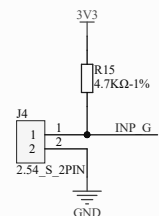
$R_{sns} = 25mV / I_{OC}$
 $R_{sns} = 25mV / 50 = 0.5mR$

过流保护50A

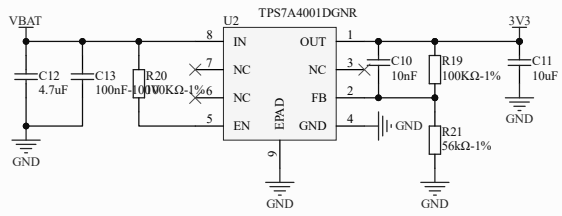
$RIWRN = 11.9 * R_{set} / (R_{sns} * I_{oc})$
 $RIWRN = 11.9 * 100R / (0.5mR * 50A) = 47600$



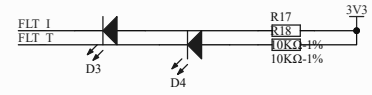
INP低：关断主MOS
INP高：开通主MOS



INP_G低：关闭预充MOS
INP_G高：开启预充MOS



$V_O = V_{ref} * (R1/R2 + 1)$
 $= 1.173V * (100/56 + 1) = 3.27V$



项目名称	ATB_HighsideSwitch_V1.0.PrjPCB			
文档名称	01_PowerCtrl.SchDoc			
日期	2025/4/30	纸号	A3	
版本	V1.0	页码	10/10	